# WOCSDICE 2018

## WORKSHOP ON COMPOUND SEMICONDUCTOR DEVICES AND INTEGRATED CIRCUITS HELD IN EUROPE

BUCHAREST, ROMANIA, 14-16 MAY 2018

# PROGRAM

| Monday, 14 May 2018 | Tuesday, 15 May 2018 | Wednesday, 16 May 2018 |
|---|---|---|
| **WOCSDICE** | **WOCSDICE** | **WOCSDICE + EXMATEC** |
| 08:30 – 09:00 WOCSDICE Registration | | 08:30 – 09:00 EXMATEC Registration |
| 09:00 – 09:15 Welcome to WOCSDICE 2018 (Mircea Dragoman, Conference Chairman) | 09:00 – 09:30 **Invited paper** (Sorin Cristoloveanu, France) | 09:00 – 09:15 Welcome to EXMATEC 2018 (Mircea Dragoman, Conference Chairman) |
| 09:15 – 09:45 **Invited paper** (Jaroslav Kovac, Slovakia) | 09:30 – 10:30 **GRAPHENE ELECTRONICS II**<br>*Chair: Sorin Cristoloveanu,* France | 09:15 – 10:15 **WOCSDICE Invited papers** (Alexandru Muller, Romania; Ikuo Soga, Japan) |
| 09:45 – 10:45 **GRAPHENE ELECTRONICS I**<br>*Chair: Hans Hartnagel, Germany* | | 10:15 – 11:15 **THZ ELECTRONICS (WOCSDICE)**<br>*Chair: Hans Hartnagel, Germany* |
| 10:45 – 11:00 **Coffee break** | 10:30 – 10:45 **Coffee break** | 11:15 – 11:30 **Coffee break** |
| 11:00 – 11:30 **Invited paper** (Gregg Jessen, USA) | 10:45 – 11:15 **Invited paper** (Alessandro Chini, Italy) | |
| 11:30 – 12:50 **DEVICES I – HEMTs**<br>*Chair: Dimitris Pavlidis, USA* | 11:15 – 12:35 **DEVICES II – GaN ELECTRONICS**<br>*Chair: Alessandro Chini, Italy* | 11:30 – 12:30 **ADVANCED MATERIALS AND APPLICATIONS III (WOCSDICE)**<br>*Chair: Alexandru Muller, Romania* |
| 13:00 – 14:00 **Lunch** | 12:45 – 14:00 **Lunch** | 12:30 – 14:00 **Lunch** |
| 14:00 – 14:30 **Invited paper** (Rusty Harris, USA) | 14:00 – 14:30 **Invited paper** (Naoteru Shigekawa, Japan) | 14:00 – 15:00 **EXMATEC Invited papers** (Robert Czernecki, Poland; Giuseppe Greco, Italy) |
| 14:30 – 15:10 **ADVANCED MATERIALS AND APPLICATIONS I**, *Chair: Titus Sandu, Romania* | 14:30 - 15:50 **HETEROSTRUCTURES**<br>*Chair: Naoteru Shigekawa, Japan* | 15:00 – 16:40 **GROWTH AND PROCESSING OF SEMICONDUCTORS AND OXIDES I (EXMATEC)**<br>*Chair: Dimitris Pavlidis, USA* |
| 15:10 – 15:30 **Coffee break** | 16:00 – 19:00 **Bucharest City Guided Tour** | |
| 15:30 – 16:50 **ADVANCED MATERIALS AND APPLICATIONS II**, *Chair: Magdalena Ciurea, Romania* | | |
| 19:00 – **WOCSDICE Welcome Cocktail**, GRAND HOTEL CONTINENTAL, Concerto Restaurant | 19:00 – **WOCSDICE Gala Dinner**, “Casa Doina” Restaurant | 19:00 – **EXMATEC Welcome Cocktail**, GRAND HOTEL CONTINENTAL, Concerto Restaurant |

| | **Monday, 14 May** |
|---|---|
| | **WOCSDICE 2018** |
| 08:30 – 09:00 | **WOCSDICE Registration** |
| 09:00 – 09:15 | **Welcome to WOCSDICE 2018**<br>Mircea Dragoman, Conference Chairman |
| 09:15 – 09:45 | **INVITED PAPER**<br>**Characterization of electrothermal properties of GaN structures supported by 2/3D electrothermal modeling and simulation**<br>Jaroslav Kovac, Institute of Electronics and Photonics, Slovak University of Technology in Bratislava, Slovakia |
| | **GRAPHENE ELECTRONICS I**<br>*Chair: Hans Hartnagel, Germany* |
| 09:45 – 10:05 | **Experimental investigations on Ni-catalyzed graphitization of PECVD deposited nanocrystalline graphene**<br>Marius A. Avram, F. Comănescu, S. Vulpe, O. Simionescu, F. Năstase, R. Gavrilă, A. Dinescu, M. Dănilă, V. Țucureanu, A. Matei, B. Țîncu, M. Veca, C. Pachiu, O. Buiu, R. Popa<br>National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania |
| 10:05 – 10:25 | **Thin film graphene nanocomposite aerogels**<br>Alexandru-Cosmin Obreja [1]*, S. Iordanescu[1], M. Popescu1, R. Gavrila[1], V. Schiopu[1], F. Comanescu [1], M. Dragoman[1]<br>[1] National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania |
| 10:25 – 10:45 | **On Graphene Nanoribbon-based Nanoelectronic Circuits Viability**<br>Sorin Cotofana[1]*, P. Dimitrakis[2], M. Enachescu[3], I. Karafyllidis[4], A. Rubio[5], G. Ch. Sirakoulis[4]<br>1 Technical University of Delft, The Netherlands; 2 Institute of Nanoscience and Nanotechnology, NCSR “Demokritos”, Greece;<br>3 “Politehnica” University of Bucharest, Romania; 4 Democritus University of Thrace, Greece;<br>5 Universitat Politècnica de Catalunya, BarcelonaTech, Spain |
| 10:45 – 11:00 | **Coffee break** |
| 11:00 – 11:30 | **INVITED PAPER**<br>**Electrical Characterization of Lateral Ga2O3 FETs for Power Switching and RF Power Applications**<br>Gregg Jessen[1]*, K. Chabak[1], A. Green, K. Leedy[1], A. Crespo[1], S. Tetlak[1], D. Walker Jr.[1], E. Heller[1]<br>[1] Air Force Research Laboratory, WPAFB, OH 45433, USA |
| | **DEVICES I – HEMTs**<br>*Chair: Dimitris Pavlidis, USA* |
| 11:30 – 11:50 | **Analysis of Thermal Properties of Power HEMT on SiC substrate**<br>Aleš Chvála1*, Robert Szobolovszký[1], Jaroslav Kováč jr. [1], Martin Florovič[1], Juraj Marek[1], Luboš Černaj[1], Patrik Príbytný[1], Daniel Donoval[1], Sylvain Laurent Delage[2], Jean-Claude Jacquet[2], Jaroslav Kováč[1]<br>[1] Institute of Electronics and Photonics, Slovak University of Technology in Bratislava, Bratislava, Slovakia<br>[2] III-V Lab, Palaiseau, France |

| | **Monday, 14 May** |
|---|---|
| | **WOCSDICE 2018** |
| 11:50 – 12:10 | **Effect of Acceptor Density in Buffer Layer on Breakdown Characteristics of AlGaN/GaN HEMTs with High-k Passivation Layer**<br>S. Ueda, Y. Kawada, K. Horio*<br>Faculty of Systems Engineering, Shibaura Institute of Technology, Saitama, Japan |
| 12:10 – 12:30 | **Analysis of microwave detection with GaN HEMTs under RF probes**<br>Hector Sánchez-Martín[1]*, E. Pérez-Martín[1], P. Altuntas[2], V Hoel[2], S. Rennesson[3], Y. Cordier[3], J. A. Novoa[1], S. Pérez[1], T. González[1], J. Mateos[1], I. Íñiguez-de-la-Torre[1]<br>[1] Universidad de Salamanca, Spain; [2] Institut d'Électronique, de microélectronique et de nanotechnologie (IEMN), France; [3] Centre de Recherche sur l'Hétéro-Epitaxie et ses Applications, CNRS-CRHEA, France |
| 12:30 – 12:50 | **High Transconductance Multiple Drain Access Channel AlGaN/GaN HEMTs**<br>Brendan Ubochi*, Kaled Ahmeda, M. Alqaysi, and K. Kalna<br>Nanoelectronic Devices Computational (NanoDeCo) Group, College of Engineering, Swansea University, Swansea, Wales, United Kingdom. |
| 13:00 – 14:00 | **Lunch** |
| 14:00 – 14:30 | **INVITED PAPER**<br>**3D (FinFET) integration of compound semiconductors with silicon**<br>Rusty Harris,Texas A&M University, USA |
| | **ADVANCED MATERIALS AND APPLICATIONS I**<br>*Chair: Titus Sandu, Romania* |
| 14:30 – 14:50 | **Low Temperature Direct Wafer Bonding of Thermally-Mismatched Materials**<br>Viorel Dragoi*, P. Kerepesi and N. Razek<br>EV Group, St. Florian am Inn, AUSTRIA |
| 14:50 – 15:10 | **Characterization of resistivity and breakdown field in Fe-doped semi-insulating GaN substrates**<br>Kosuke Suzuki[1], Atsuki Aoai[1], Joel T. Asubar[1], Hirokuni Tokuda[1], Kohei Nojima[2], Naoto Ishibashi[2], Narihito Okada[2], Kazuyuku Tadatomo[2], Masaaki Kuzuhara[1]<br>[1] University of Fukui, Fukui, Japan; [2] Yamaguchi University, Yamaguchi, Japan |
| 15:10 – 15:30 | **Coffee break** |
| | **ADVANCED MATERIALS AND APPLICATIONS II**<br>*Chair: Magdalena Ciurea, Romania* |
| 15:30 – 15:50 | **Ion Implantation for adjusting electrical conductivity of β-Ga2O3 by Nitrogen and Germanium Incorporation**<br>Kornelius Tetzner[1], E. Bahat-Treidel[1], A. Thies[1], G. Wagner[2], J. Würfl[1]<br>[1]Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik, Berlin, Germany; 2Leibniz-Institut für Kristallzüchtung (IKZ), Berlin, Germany |

|  | **Monday, 14 May** |
|---|---|
|  | **WOCSDICE 2018** |
| 15:50 – 16:10 | **Models of thermal conductivity in ultrananocrystalline diamond films**<br>Titus Sandu*, Cristina Pachiu, Mihai Gologanu<br>National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania |
| 16:10 – 16:30 | **Impact of thermal treatment upon morphology and crystallinity of titanium nitride thin films deposited by RF sputtering**<br>Silviu Vulpe[1]*, F. Nastase[1], A. Avram[1], O. Simionescu[1], C. Romanitan[1], R. Gavrila[1], B. Bita[1,2], A. Dumitru[2]<br>[1] National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania<br>[2] Faculty of Physics, University of Bucharest, PO Box MG-11, 077125, Magurele, Romania |
| 16:30 – 16:50 | **Dielectrics choice and processing for low dispersion enhancement mode p-GaN gate HEMTs on 200mm Si substrates**<br>Shuzhen You[1]*, N. E. Posthuma[1], N. Ronchi[1], S. Stoffels[1], B. Bakeroot[2], D. Wellekens[1], H. Liang[1], M. Zhao[1], S. Decoutere[1]<br>[1] IMEC, Leuven, Belgium; 2 Centre for Microsystems Technology (CMST), IMEC and Ghent University, Gent, Belgium |
| 19:00 – 21:00 | **WOCSDICE Welcome Cocktail,** GRAND HOTEL CONTINENTAL, Concerto Restaurant |

| | **Tuesday, 15 May** |
|---|---|
| | **WOCSDICE 2018** |
| 09:00 – 09:30 | **INVITED PAPER**<br>**Novel concepts for nano-devices**<br>Sorin Cristoloveanu and Maryline Bawedin<br>IMEP-LAHC, Grenoble INP Minatec, Grenoble, France<br><br>**GRAPHENE ELECTRONICS II**<br>*Chair: Sorin Cristoloveanu,* France |
| 09:30 – 09:50 | **Graphene self-switching diodes for sub-millimetre wave harvesting applications**<br>Martino Aldrigo[1]*, M. Yasir[2], S. Iordanescu[1], D. Vasilache[1], A. Dinescu[1], M. Dragoman[1], M. Bozzi[2]<br>[1] National Institute for Research and Development in Microtechnologies - IMT Bucharest, Romania; [2] University of Pavia, Pavia, Italy |
| 09:50 – 10:10 | **Two-Dimensional Layered Approaches for Devices Operating Using the Valley Degree of Freedom**<br>P. Sengupta[1], J. Shi[1] and Dimitris Pavlidis[2]*<br>1 University of Illinois, Chicago, Illinois, USA; 2 Boston University, Boston, Massachusetts, USA |
| 10:10 – 10:30 | **Detection of $CO_2$ Using MWCNT-Based Sensors**<br>Alina Cismaru[1]*, C. Obreja[1], M. Aldrigo[1], S. Iordanescu[1], B. Bita[1], M. Dragoman[1]<br>[1] National Institute for Research and Development in Microtechnologies – IMT Bucharest, Romania |
| 10:30 – 10:45 | **Coffee break** |
| 10:45 – 11:15 | **INVITED PAPER**<br>**GaN RF and GaN Power – Device Parameter Drifts Analysis**<br>Alessandro Chini, *University of Modena and Reggio Emilia, Italy*<br><br>**DEVICES II – GaN ELECTRONICS**<br>*Chair: Alessandro Chini, Italy* |
| 11:15 – 11:35 | **Ni based Schottky contacts in bulk GaN**<br>Giuseppe Greco[1], F. Giannazzo[1], M. Spera[1,2,3], M. Cannas[3], A. Alberti[1], F. Iucolano[4], F. Roccaforte[1]<br>1 Istituto per la Microelettronica e Microsistemi (CNR-IMM), Catania, Italy; 2 University of Catania, Catania, Italy; 3 University of Palermo, Palermo, Italy; 4 STMicroelectronics, Catania, Italy |
| 11:35 – 11:55 | **Fabrication of quasi-vertical GaN JFET via Selective-Area Regrowth**<br>Simon Kotzea*[1], A. Debald[1], M. Heuken[1, 2], H. Kalisch[1] and A. Vescan[1]<br>1 CST, RWTH Aachen University, Aachen, Germany; 2 AIXTRON SE, Herzogenrath, Germany |

| | **Tuesday, 15 May** |
|---|---|
| | **WOCSDICE 2018** |
| 11:55 – 12:15 | **Self-Aligned Processing of p-GaN-Gated E-mode HFET by Selective Etching with $Cl_2/O_2/N_2$**<br>Gerrit Lükens[1*], H. Hahn[1], M. Eickelkamp[2], M. Heuken[1,2], H. Kalisch[1] and A. Vescan[1]<br>1 CST, RWTH Aachen University, Aachen, Germany; 2 AIXTRON SE, Germany |
| 12:15 – 12:35 | **Reduction of threshold voltage for accumulation drifts in n-GaN MIS capacitors devices by post-metallization annealing**<br>Nicole Volkmer[1], Eldad Bahat Treidel[1], Franziska Naumann[2], Hassan Gargouri[2], Ina Ostermay[1], Oliver Hilt[1] and Joachim Würfl[1]<br>1 Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik, Berlin, Germany<br>2 SENTECH Instruments GmbH, Berlin, Germany |
| 12:45 – 14:00 | **Lunch** |
| 14:00 – 14:30 | **INVITED PAPER**<br>**Hybrid heterostructures and heterostructure devices fabricated by surface activated bonding technologies**<br>Naoteru Shigekawa, *Graduate School of Engineering, Osaka City University, Japan*<br><br>**HETEROSTRUCTURES**<br>*Chair: Naoteru Shigekawa, Japan* |
| 14:30 – 14:50 | **Optical properties of as-grown GaAs/GaAsBi single quantum well structures grown by Molecular Beam Epitaxy**<br>Haifa Alghamdi1*, M. Henini1, D. Fan2, 3, Y. I. Mazur3, M. E. Ware2, 3, S.-Q. Yu2, 3, G. J. Salamo3<br>1 University of Nottingham, Nottingham, UK; 2 Department of Electrical Engineering, University of Arkansas, Fayetteville, AR, USA.<br>3 Institute for Nanoscience and Engineering, University of Arkansas, Fayetteville, AR, USA |
| 14:50 – 15:10 | **Coupling study in type II GaSb/GaAs quantum ring solar cells**<br>D. Montesdeoca[1*], P.D. Hodgson[1], M. De La Mata[2], A.R.J. Marshall[1], S.I. Molina[2], P.J. Carrington[3] and A. Krier[1]<br>1 Physics Department, Lancaster University, Lancaster, UK; 2 Facultad de Ciencias, IMEYMAT, Universidad de Cadiz, Campus Rio san Pedro, Cadiz, Spain; 3 Engineering Department, Lancaster University, Lancaster, UK |
| 15:10 – 15:30 | **Broadband terahertz source based on wide-bandgap semiconductor quantum cascade structures for the detection of explosive materials**<br>Hans L. Hartnagel[1*] and Vadim P. Sirkeli1,2<br>1 Institut für Mikrowellentechnik und Photonik, Technische Universität Darmstadt, Darmstadt, Germany<br>2 Department of Information Technologies, Mathematics and Physics, Comrat State University, Comrat, Moldova |
| 15:30 – 15:50 | **Sheet resistance under Ohmic contacts on AlGaN/GaN heterostructures**<br>Monia Spera[1,2,3,*], G. Greco [1], C. Miccoli[4], R. Lo Nigro[1], C. Bongiorno[1], D. Corso [1], S. Di Franco [1], F. Iucolano [4], F. Roccaforte[1]<br>1 Istituto per la Microelettronica e Microsistemi (CNR-IMM), Catania, Italy; 2 University of Catania, Catania, Italy; 3 University of Palermo, Palermo, Italy; 4 STMicroelectronics, Catania, Italy |
| 16:00 – 19:00 | **Bucharest City Guided Tour** |
| 19:00 – 22:00 | **WOCSDICE Gala Dinner**, “Casa Doina” Restaurant |

| | **Wednesday, 16 May** |
|---|---|
| | **WOCSDICE + EXMATEC 2018** |
| **08:30 – 09:00** | **EXMATEC Registration** |
| 09:00 – 09:15 | **Welcome to EXMATEC 2018**<br>Mircea Dragoman, Conference Chairman |
| | **WOCSDICE INVITED PAPERS** |
| 09:15 – 09:45 | **GaN SAW based sensors manufactured by micromachining and nanoprocesing of of GaN/Si**<br>Alexandru Muller, National Institute for R&D in Microtechnologies - IMT Bucharest, Romania |
| 09:45 – 10:15 | **MM-W and THz Circuitry Designs Based on InP and CMOS**<br>Ikuo Soga[1]*, Yoichi Kawano[1]<br>1 Devices & Materials Laboratory, Fujitsu Laboratories Limited |
| | **THZ ELECTRONICS I (WOCSDICE)**<br>*Chair: Hans Hartnagel, Germany* |
| 10:15 – 10:35 | **Resonant tunneling hard-type oscillators having a Schottky diode trigger circuit for stable and large voltage swing operation**<br>Koichi Maezawa*, Motoyuki Yoshida, Masayuki Mori<br>1 Graduate School of Science and Engineering, University of Toyama |
| 10:35 – 10:55 | **Near-ultraviolet avalanche photodetectors based on bulk ZnSe**<br>Hans L. Hartnagel[1]*, Vadim P. Sirkeli[1,2], Oktay Yilmazoglu[3], Ahid S. Hajo[1], Natalia D. Nedeoglo[4], Dmitrii D. Nedeoglo[4], Sascha Preu[1], and Franko Küppers[1]<br>1 Institut für Mikrowellentechnik und Photonik, Technische Universität Darmstadt, Darmstadt, Germany; 2 Comrat State University, Comrat, Moldova; 3 Department of High Frequency Electronics, Technische Universität Darmstadt, Darmstadt, Germany; 4 Moldova State University, Chisinau, Moldova |
| 10:55 – 11:15 | **A novel mechanical tuning element for SIW applications**<br>Valentin Buiculescu, Ioana Zdru, *National Institute for R&D in Microtechnologies - IMT Bucharest, Romania* |
| 11:15 – 11:30 | **Coffee break** |
| | **ADVANCED MATERIALS AND APPLICATIONS III (WOCSDICE)**<br>*Chair: Alexandru Muller, Romania* |
| 11:30 – 11:50 | **Effect of silicon surface cleaning on reliability of ALD HfO2 films deposited from Tetrakis(dimethylamino)hafnium (TDMAH)**<br>Cornel Cobianu[1,2], Florin Nastase[1,2], Niculae Dumbravescu[1,2], Octavian Buiu[1,2], Bogdan Serban[1,2], Florin Comanescu[1], Raluca Gavrila[1], Cosmin Romanitan[1], Octavian Ionescu[1,2];<br>1.National Institute for Research and Development in Microtechnologies - IMT Bucharest, ROMANIA<br>2.Research Centre for Integrated Systems, Nanotechnologies and Carbon Based Nanomaterials (CENASIC) - IMT Bucharest, ROMANIA, |

|  | **Wednesday, 16 May** |
|---|---|
|  | **WOCSDICE + EXMATEC 2018** |
| 11:50 – 12:10 | **Comparative study of structural and optical properties of Sm and La doped ZnO**<br>P. Pascariu[1], I. V. Tudose[2], C. Pachiu[3], M. Danila[3], R. Gavrila[3], E. Koudoumas[2], Mirela Suchea [2,3]*<br>1 ”Petru Poni” Institute of Macromolecular Chemistry, Iaşi, Romania; 2 Technological Educational Institute of Crete, Heraklion, Greece<br>3 National Institute for Research and Development in Microtechnologies - IMT Bucharest, Bucharest, Romania |
| 12:10 – 12:30 | **Semiconducting metal oxides for ammonia and aliphatic amines gas sensing. A novel HSAB interaction paradigm**<br>B. C. Serban[1]*, O. Buiu[1], O. Ionescu[1], C. Cobianu[1], M. Brezeanu[2]<br>1 National Institute for Research and Development in Microtechnologies - IMT Bucharest, Romania; 2 University Politehnica of Bucharest, Romania |
| 12:30 – 14:00 | **Lunch** |
|  | **EXMATEC INVITED PAPERS** |
| 14:00 – 14:30 | **Influence of hydrogen on InGaN quantum well MOVPE growth**<br>Robert Czernecki[1,2*], E. Grzanka[1,2], J. Smalc-Koziorowska[1,2], S. Grzanka[1,2], M. Leszczynski[1,2]; [1]Institute of High Pressure Physics of the Polish Academy of Sciences, Poland; [2]TopGaN Ltd., Poland |
| 14:30 – 15:00 | **Ohmic metallizations for GaN-based devices**<br>Giuseppe Greco[1]*, F. Iucolano[2], F. Roccaforte[1]; [1]Consiglio Nazionale delle Ricerche – Istituto per la Microelettronica e Microsistemi (CNR-IMM), Italy; [2]STMicroelectronics, Italy |
|  | **GROWTH AND PROCESSING OF SEMICONDUCTORS AND OXIDES I (EXMATEC)**<br>*Chair: Dimitris Pavlidis, USA* |
| 15:00 – 15:20 | **Preparation of ZnO:Al thin films by helicon wave excited magnetron sputtering method**<br>Shizutoshi Ando*, T. Namba, Tokyo University of Science, Japan |
| 15:20 – 15:40 | **Oxide-free, electrically-conductive semiconductor interfaces fabricated by room temperature covalent direct bonding**<br>Viorel Dragoi*, C. Flötgen, N. Razek, EV Group E. Thallner GmbH, Austria |
| 15:40 – 16:00 | **Atomic layer etching of AlGaN**<br>Sebastien Aroulanda[1,2]*, O. Patard[1], N. Defrance[2], P. Altuntas[1], N. Michel[1], J. Pereira[1], P. Gamarra[1], C. Lacam[1], S. L. Delage[1], J.-C. de Jaeger[2], C. Gaquiere[2], [1]III-V Lab, France ; [2]Institut d’Electronique, de Microélectronique et de Nanotechnologie, France |
| 16:00 – 16:20 | **MOCVD growth of thick InxAl1-xN (0.37 ≤ x ≤ 0.40) layer**<br>Prerna Chauhan[1]*, S. Hasenöhrl[1], E. Dobročka[1], J. Kuzmík[1]; [1]Institute of Electrical Engineering, Slovak Academy of Sciences, Slovak Republic |
| 16:20 – 16:40 | **Nanoscale electrical characterization of graphene Schottky contacts onto AlGaN/GaN heterostructures**<br>G. Greco[1*], E. Schilirò[1], S. Di Franco[1], R. Lo Nigro[1], F. Roccaforte[1], F. Giannazzo[1], F. Iucolano[2], S. Ravesi[2], P. Prystawko[3], P. Kruszewski[3], M. Leszczyński[3], R. Dagher[4], E. Frayssinet[4], A. Michon[4], Y. Cordier[4]; [1]Consiglio Nazionale delle Ricerche – Istituto per la Microelettronica e Microsistemi (CNR-IMM), Italy, [2]STMicroelectronics, Italy; [3]TopGaN, Poland; [4]Université Côte d’Azur, CNRS, CRHEA, France |
| 19:00 – 21:00 | **EXMATEC Welcome Cocktail**, GRAND HOTEL CONTINENTAL, Concerto Restaurant |